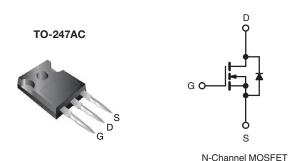
Vishay Siliconix

Power MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	200		
$R_{DS(on)}(\Omega)$	V _{GS} = 10 V	0.18	
Q _g (max.) (nC)	70		
Q _{gs} (nC)	13		
Q _{gd} (nC)	39		
Configuration	Single		

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- · Isolated central mounting hole
- · Fast switching
- · Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFP240PbF

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V _{DS}	200	V
Gate-source voltage			V_{GS}	± 20	V
Continuous drain current	V _{GS} at 10 V	$T_{\rm C} = 25 ^{\circ}{\rm C}$ $T_{\rm C} = 100 ^{\circ}{\rm C}$		20	
Continuous drain current	V _{GS} at 10 V	T _C = 100 °C	I _D	12	Α
Pulsed drain current ^a			I _{DM}	80	
Linear derating factor				1.2	W/°C
Single pulse avalanche energy b			E _{AS}	510	mJ
Repetitive avalanche current ^a			I _{AR}	20	Α
Repetitive avalanche energy ^a			E _{AR}	15	mJ
Maximum power dissipation $T_C = 25 ^{\circ}C$			P _D	150	W
Peak diode recovery dV/dt ^c			dV/dt	5.0	V/ns
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) ^d for 10 s				300 ^d	
Mounting torque			10	lbf ⋅ in	
	6-32 or M3 screw			1.1	N⋅m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. V_{DD} = 50 V, starting T_J = 25 °C, L = 1.9 mH, R_g = 25 Ω , I_{AS} = 20 A (see fig. 12)
- c. $I_{SD} \le 18$ A, $dI/dt \le 150$ A/µs, $V_{DD} \le V_{DS}$, $T_{J} \le 150$ °C
- d. 1.6 mm from case



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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R _{thJA}	-	40	
Case-to-sink, flat, greased surface	R _{thCS}	0.24	-	°C/W
Maximum junction-to-case (drain)	R _{thJC}	-	0.83	

PARAMETER	SYMBOL	TEST (CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 2$	50 μΑ	200	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to 25	°C, I _D = 1 mA	-	0.29	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 2$	250 μA	2.0	-	4.0	V
Gate-source leakage	I _{GSS}	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 200 \text{ V}, V_{GS}$ $V_{DS} = 160 \text{ V}, V_{GS}$	S = 0 V S = 0 V, T _J = 125 °C	-	-	25 250	μA
Drain-source on-state resistance	R _{DS(on)}		I _D = 12 A ^b	-	-	0.18	Ω
Forward transconductance	9fs	$V_{DS} = 50 \text{ V}, I_{D} =$	12 A ^b	6.9	-	-	S
Dynamic					I.	•	
Input capacitance	C _{iss}	$V_{GS} = 0 V$		-	1300	-	
Output capacitance	C _{oss}	$V_{DS} = 25 \text{ V},$		-	400	-	рF
Reverse transfer capacitance	C _{rss}	f = 1.0 MHz, see	fig. 5	-	130	-	
Total gate charge	Q _g			-	-	70	
Gate-source charge	Q _{qs}	V _{GS} = 10 V	$V_{GS} = 10 \text{ V}$ $I_D = 18 \text{ A}, V_{DS} = 160 \text{ V},$ see fig. 6 and 13 b	-	-	13	nC
Gate-drain charge	Q _{qd}	See lig. 6 and 13	-	-	39		
Turn-on delay time	t _{d(on)}	· ·		-	14	-	
Rise time	t _r	$V_{DD} = 100 \text{ V}, I_D =$		-	51	-	1
Turn-off delay time	t _{d(off)}	$R_g = 9.1 \ \Omega, R_D = 5.4 \ \Omega,$ see fig. 10^{b}		-	45	-	ns
Fall time	t _f			-	36	-	
Internal drain inductance	L _D	Between lead,	الم ا	-	5.0	-	
Internal source inductance	L _S		6 mm (0.25") from package and center of		13	-	nH
Drain-Source Body Diode Characteristic	cs						
Continuous source-drain diode current	I _S	MOSFET symbo	_ 10	-	-	20	
Pulsed diode forward current ^a	I _{SM}	showing the integral reverse p - n junction diode		-	-	80	А
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 2	20 A, V _{GS} = 0 V ^b	-	-	2.0	V
Body diode reverse recovery time	t _{rr}	T 05 °C '	10 A -11/-14 - 100 A / - b	-	300	610	ns
Body diode reverse recovery charge	Q _{rr}	$T_J = 25 ^{\circ}\text{C}, I_F = 18 \text{A}, dI/dt = 100 \text{A/}\mu\text{s}^{\text{b}}$		-	3.4	7.1	μC
Forward turn-on time	t _{on}	Intrinsic turn-on	time is negligible (turn-on	is domin	ated by L	s and L _D)	

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width \leq 300 µs; duty cycle \leq 2 %



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

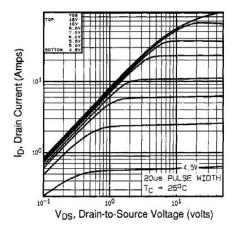


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

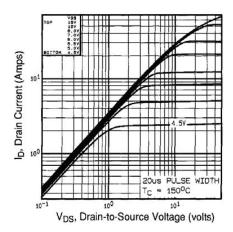


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

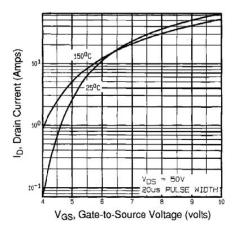


Fig. 3 - Typical Transfer Characteristics

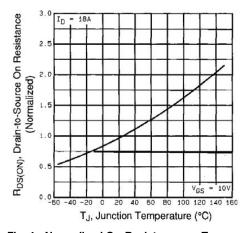


Fig. 4 - Normalized On-Resistance vs. Temperature

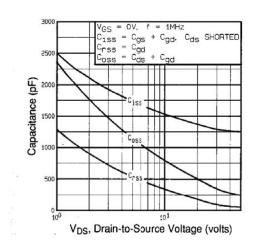


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

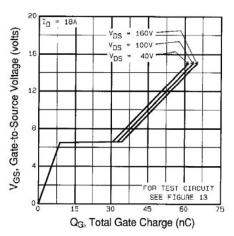


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



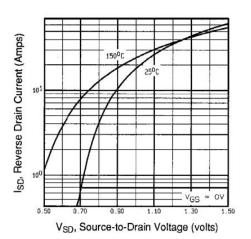


Fig. 7 - Typical Source-Drain Diode Forward Voltage

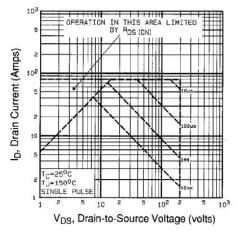


Fig. 8 - Maximum Safe Operating Area

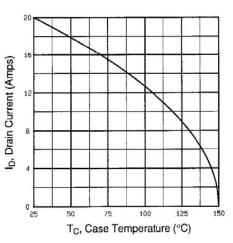


Fig. 9 - Maximum Drain Current vs. Case Temperature

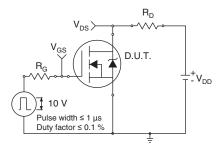


Fig. 10a - Switching Time Test Circuit

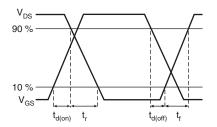


Fig. 10b - Switching Time Waveforms

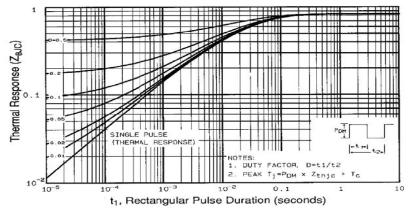


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



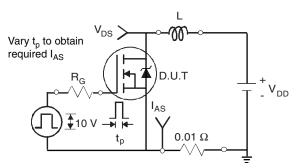


Fig. 12a - Unclamped Inductive Test Circuit

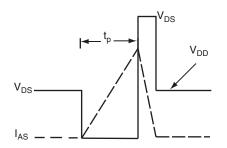


Fig. 12b - Unclamped Inductive Waveforms

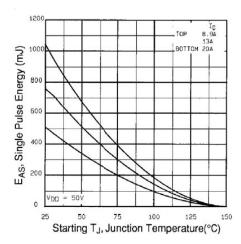


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

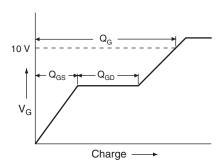


Fig. 13a - Basic Gate Charge Waveform

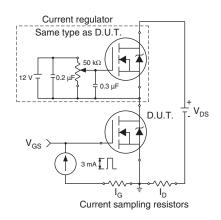


Fig. 13b - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit

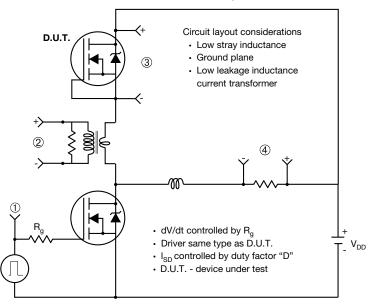




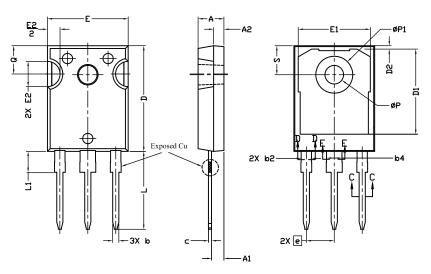
Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg291210.

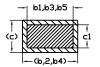


TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C, D--D, E--E

	MILLIN		
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

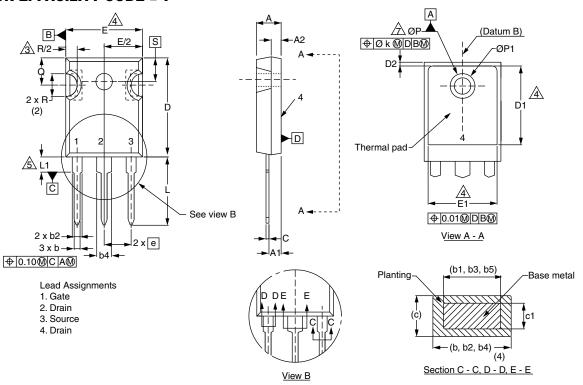
MILLIMETERS		
MIN.	MAX.	NOTES
16.25	16.85	5
0.56	0.76	
15.50	15.87	4
13.46	14.16	5
4.52	5.49	3
5.44	BSC	
14.90	15.40	
3.96	4.16	6
3.56	3.65	7
7.19 ref.		
5.31	5.69	
5.54	5.74	
	MIN. 16.25 0.56 15.50 13.46 4.52 5.44 14.90 3.96 3.56 7.19	MIN. MAX. 16.25 16.85 0.56 0.76 15.50 15.87 13.46 14.16 4.52 5.49 5.44 BSC 14.90 15.40 3.96 4.16 3.56 3.65 7.19 ref. 5.31 5.69

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$ Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

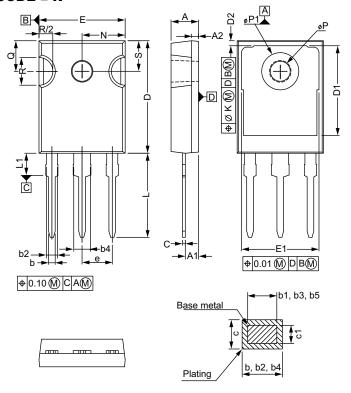
	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
Е	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.254		
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.2	54	
L	14.20	16.10	
L1	3.71	4.29	
N	7.62 BSC		
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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